

$V_{DSS}$	-30V
$R_{DS(on)}(Max.)$	91mΩ
$I_D$	±2.5A
$P_D$	1W

### ●Features

- 1) Low on - resistance.
- 2) Small Surface Mount Package (TSMT3).
- 3) Pb-free lead plating ; RoHS compliant

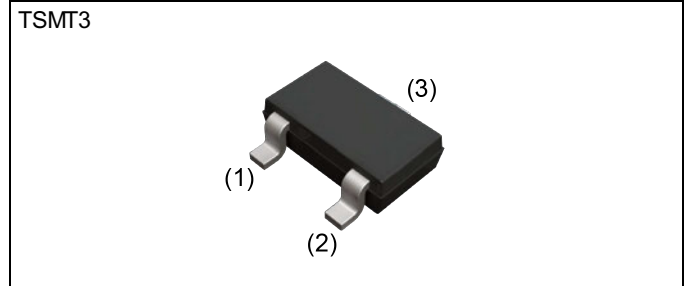
### ●Application

Switching

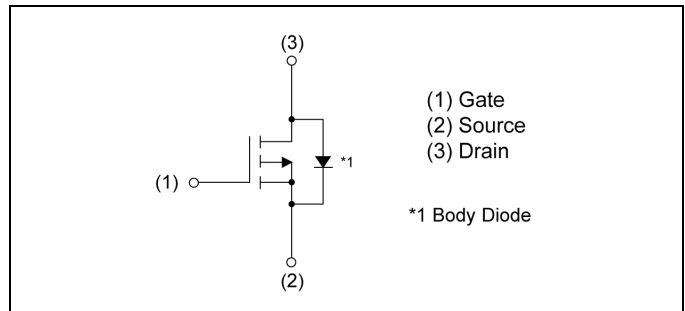
### ●Absolute maximum ratings ( $T_a = 25^\circ C$ )

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{DSS}$	-30	V
Continuous drain current	$I_D$	±2.5	A
Pulsed drain current	$I_{D,pulse}^{*2}$	±12	A
Gate - Source voltage	$V_{GSS}$	±20	V
Avalanche energy, single pulse	$E_{AS}^{*3}$	4.5	mJ
Avalanche current	$I_{AS}^{*3}$	-2.5	A
Power dissipation	$P_D^{*4}$	1	W
Junction temperature	$T_j$	150	°C
Range of storage temperature	$T_{stg}$	-55 to +150	°C

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TCL
	Marking	JS

### ● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	$R_{thJA}^{*4}$	-	125	-	°C/W

### ● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -1mA$	-30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = -1mA$ referenced to $25^\circ\text{C}$	-	-22	-	mV/°C
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$	-	-	-1	μA
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -1mA$	-1.0	-	-2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = -1mA$ referenced to $25^\circ\text{C}$	-	2.9	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = -10V, I_D = -2.5A$	-	70	91	mΩ
		$V_{GS} = -4.5V, I_D = -2.5A$	-	104	135	
Transconductance	$g_{fs}^{*5}$	$V_{DS} = -5V, I_D = -2.5A$	2.1	-	-	S

\*1 Limited only by maximum temperature allowed.

\*2  $P_w \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*3  $L \approx 1\text{mH}$ ,  $V_{DD} = -15V$ ,  $R_G = 25\Omega$ , STARTING  $T_{ch} = 25^\circ\text{C}$  Fig.3-1,3-2

\*4 Mounted on a ceramic boad (30×30×0.8mm)

\*5 Pulsed

**● Electrical characteristics** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	$C_{iss}$	$V_{GS} = 0V$	-	220	-	pF
Output capacitance	$C_{oss}$	$V_{DS} = -15V$	-	45	-	
Reverse transfer capacitance	$C_{rss}$	$f = 1\text{MHz}$	-	35	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx -15V, V_{GS} = -10V$	-	6.5	-	ns
Rise time	$t_r^{*5}$	$I_D = -1.25A$	-	8.5	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 12\Omega$	-	22	-	
Fall time	$t_f^{*5}$	$R_G = 10\Omega$	-	5.5	-	

**● Gate charge characteristics** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit	
			Min.	Typ.	Max.		
Total gate charge	$Q_g^{*5}$	$V_{DD} \approx -15V$	$V_{GS} = -10V$	-	5.4	-	nC
Gate - Source charge	$Q_{gs}^{*5}$	$I_D = -2.5A$	$V_{GS} = -4.5V$	-	2.7	-	
Gate - Drain charge	$Q_{gd}^{*5}$			-	0.8	-	
				-	1.0	-	

**● Body diode electrical characteristics** (Source-Drain) ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	$I_S^{*1}$	$T_a = 25^\circ\text{C}$	-	-	-0.8	A
Body diode pulse current	$I_{SP}^{*2}$		-	-	-12	
Forward voltage	$V_{SD}^{*5}$	$V_{GS} = 0V, I_S = -0.8A$	-	-	-1.2	V

● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

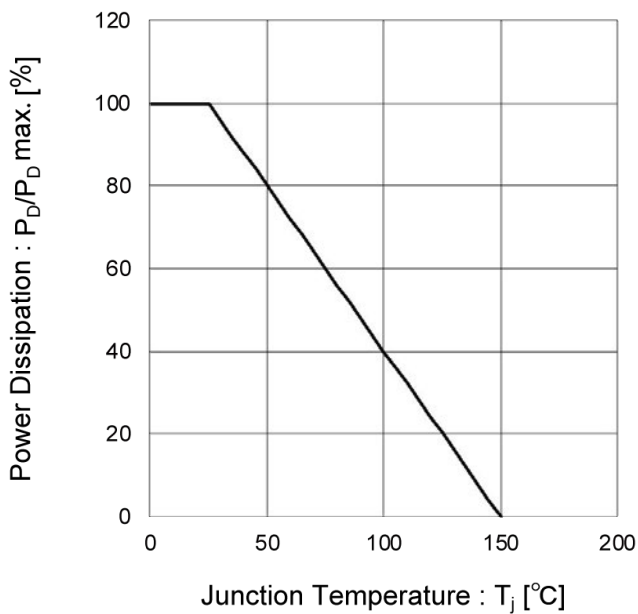


Fig.2 Maximum Safe Operating Area

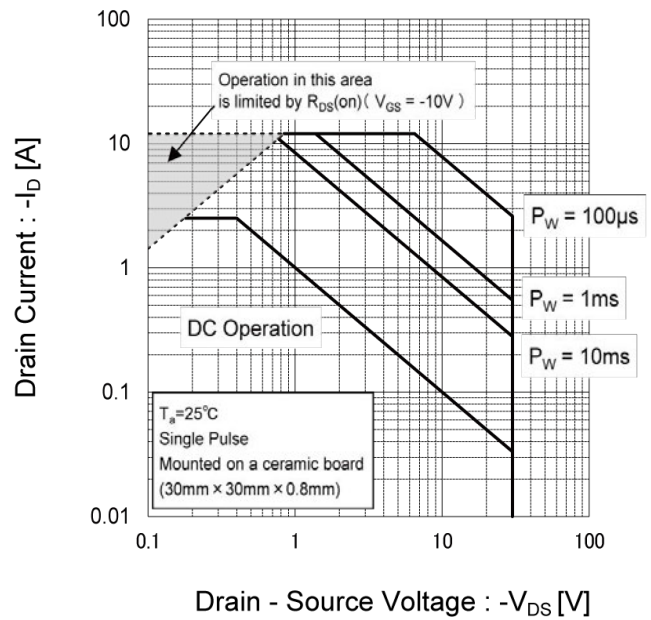


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

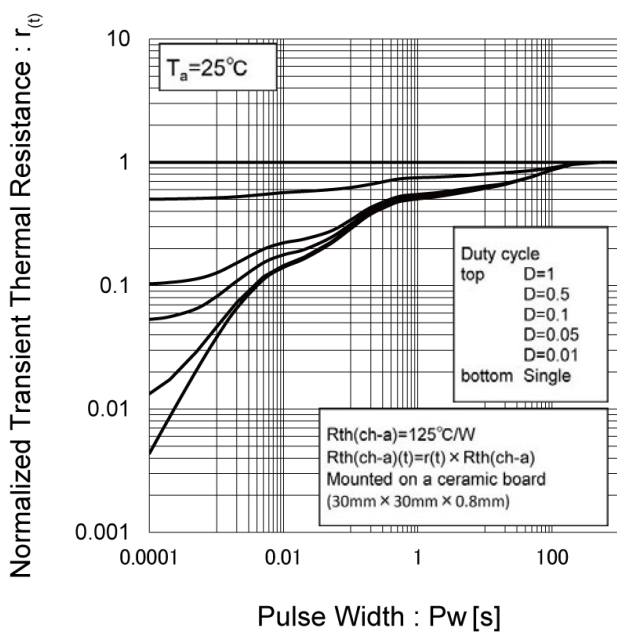
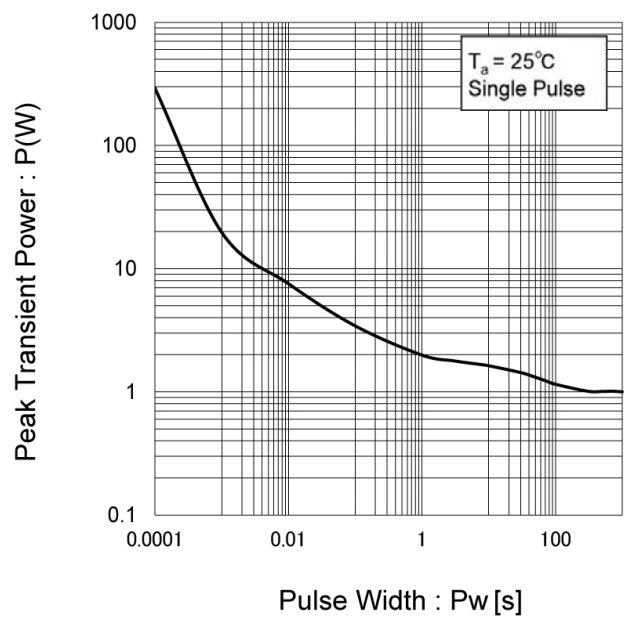


Fig.4 Single Pulse Maximum Power dissipation



● Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

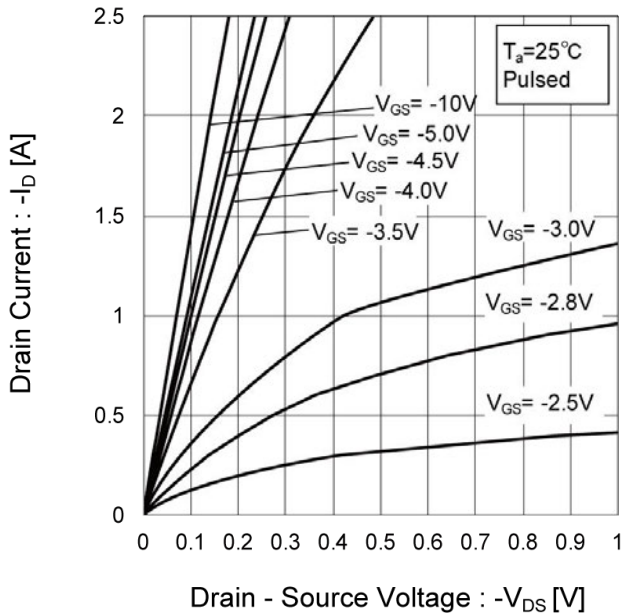


Fig.6 Typical Output Characteristics(II)

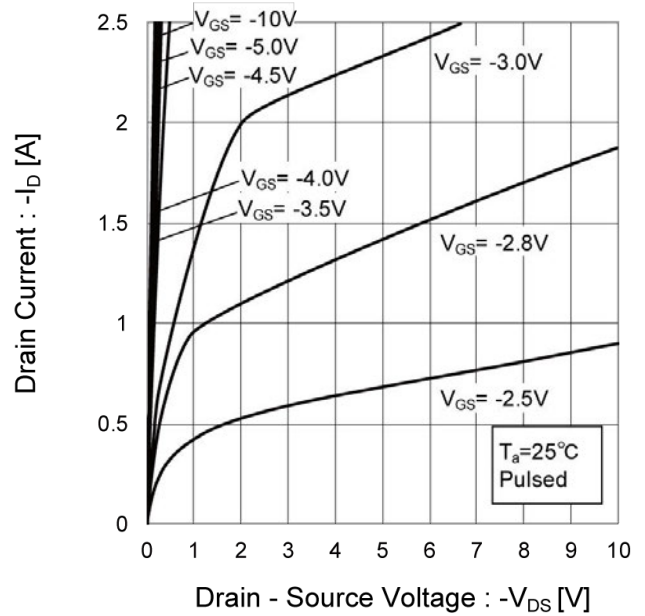
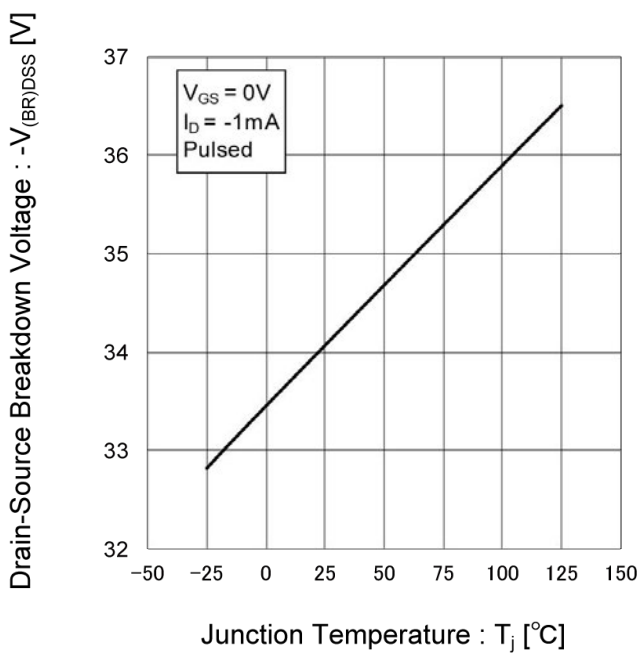


Fig.7 Breakdown Voltage vs. Junction Temperature



● Electrical characteristic curves

Fig.8 Typical Transfer Characteristics

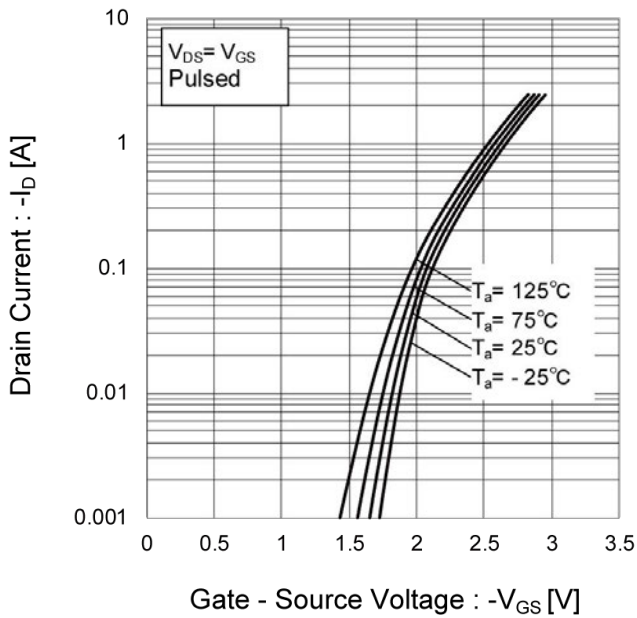


Fig.9 Gate Threshold Voltage vs. Junction Temperature

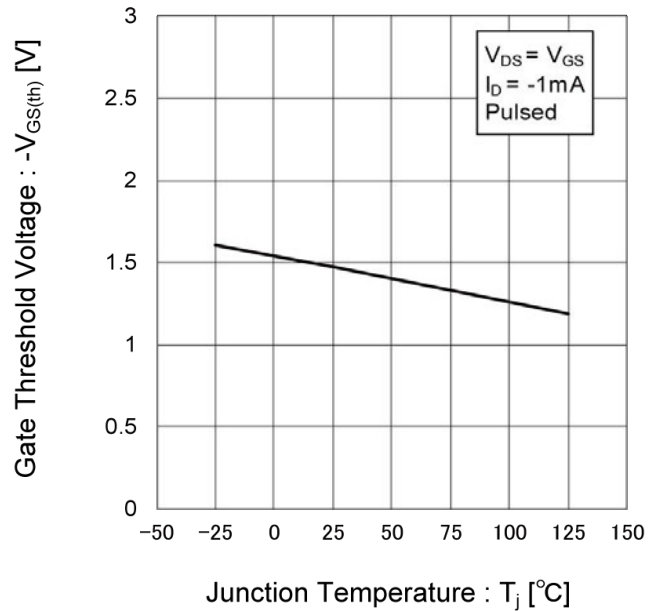
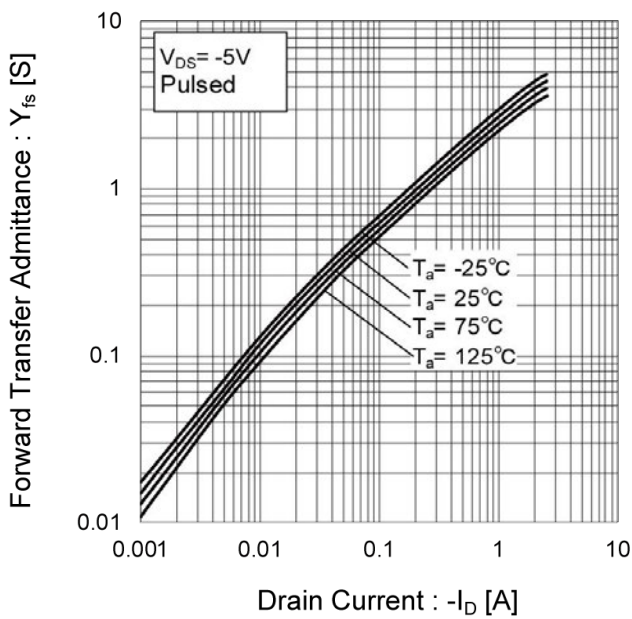


Fig.10 Transconductance vs. Drain Current



● Electrical characteristic curves

Fig.11 Drain Current Derating Curve

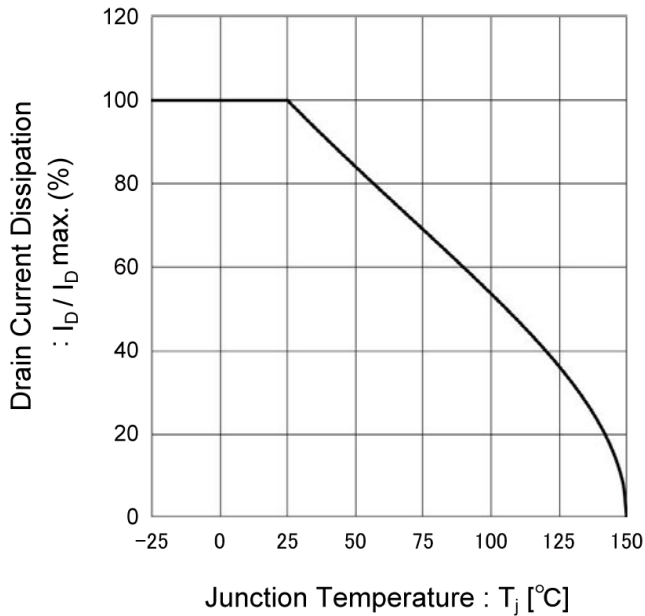


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

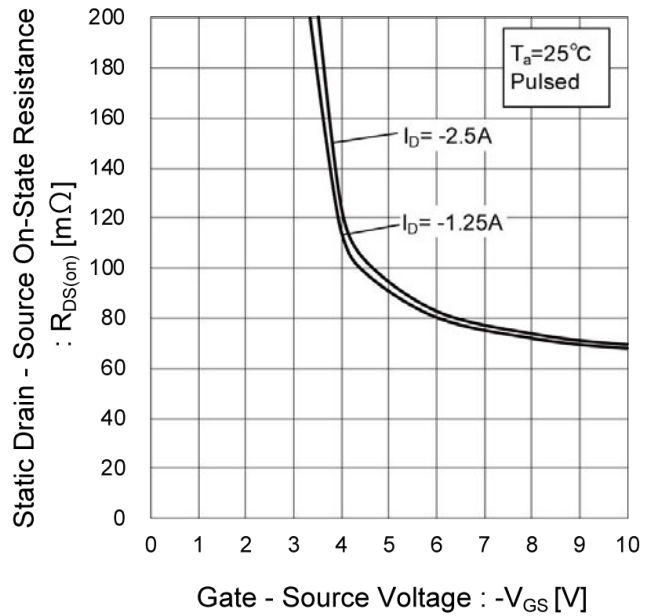
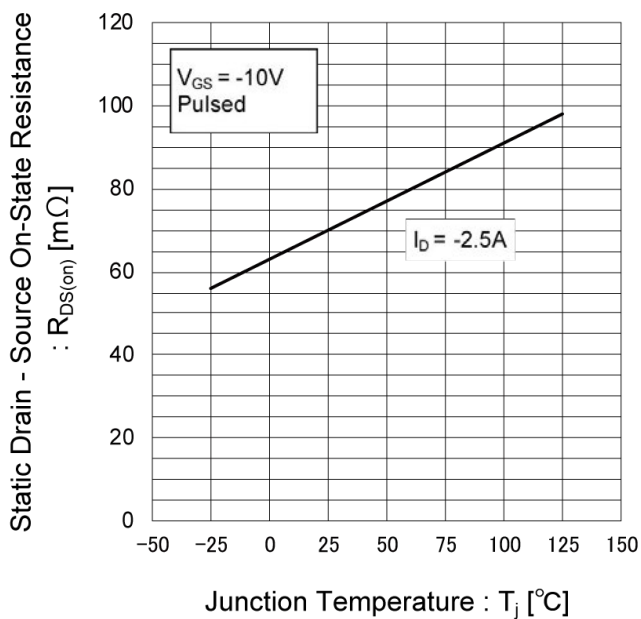


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



● Electrical characteristic curves

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

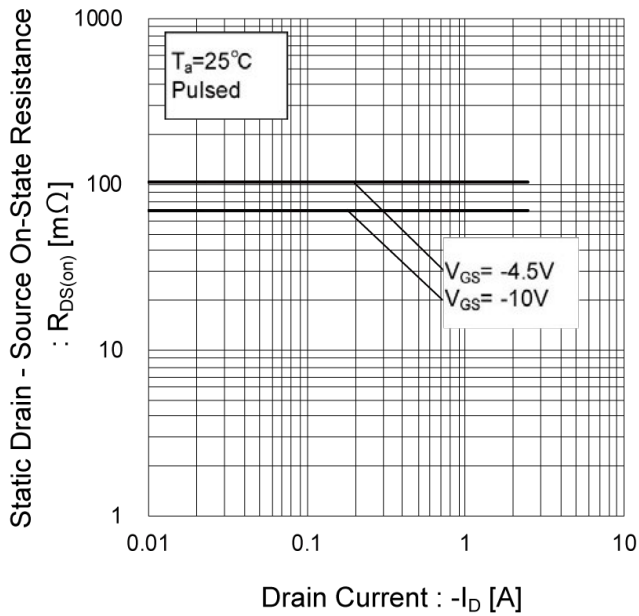


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

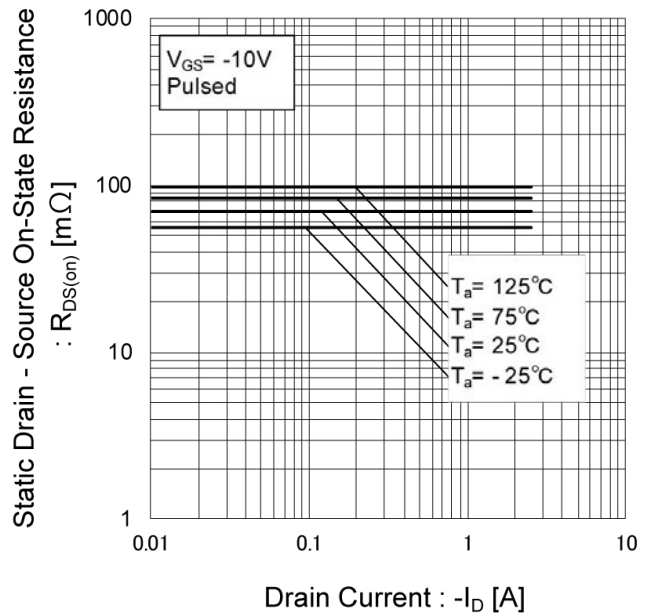
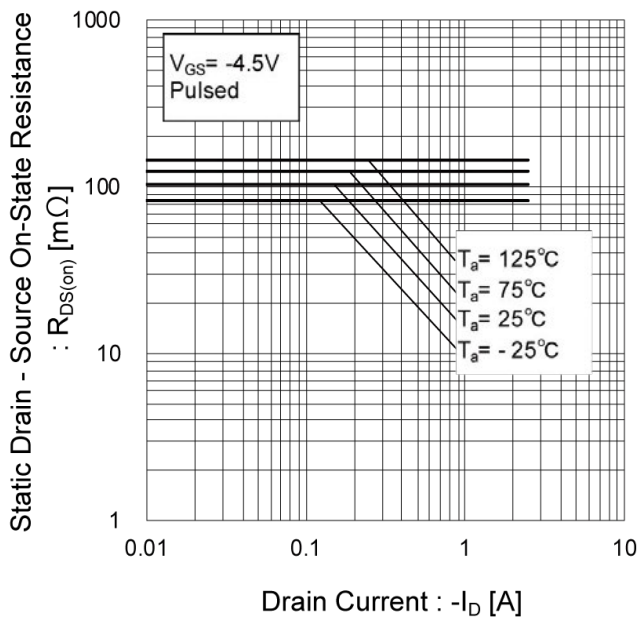


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)





●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

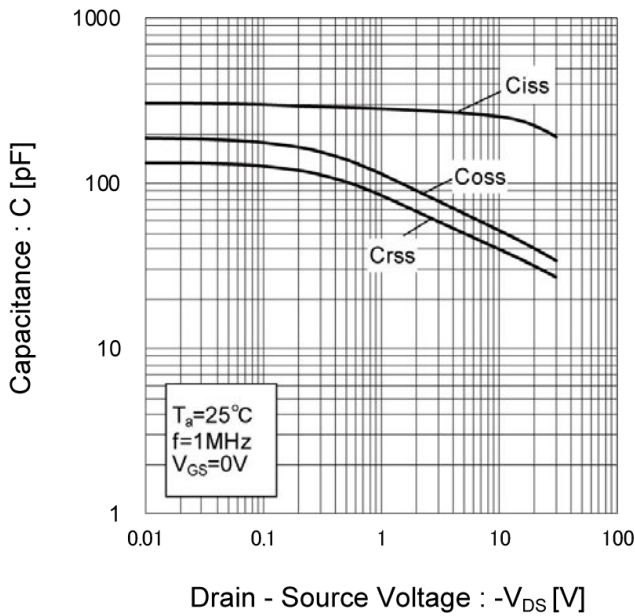


Fig.18 Switching Characteristics

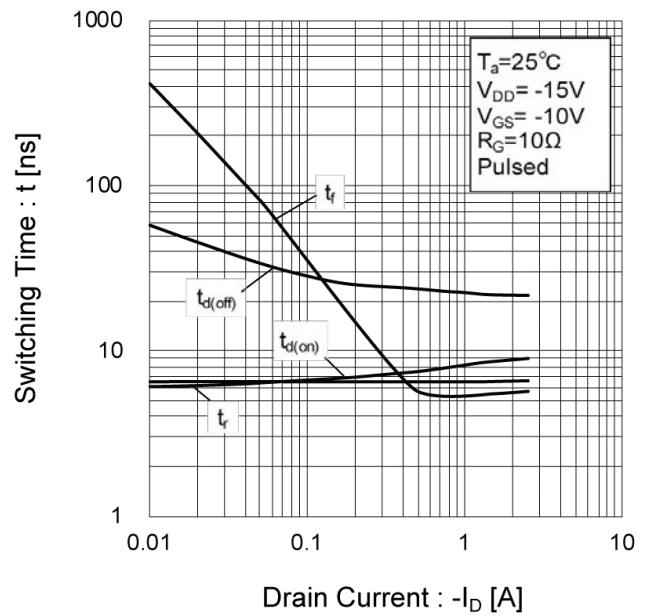


Fig.19 Dynamic Input Characteristics

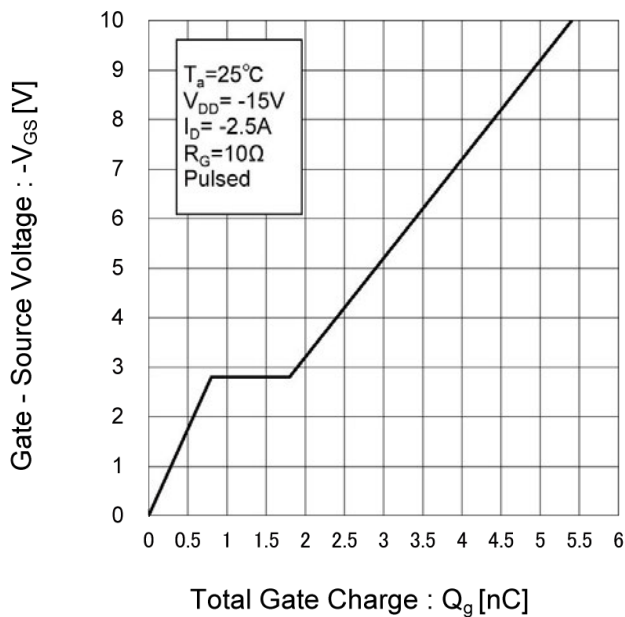
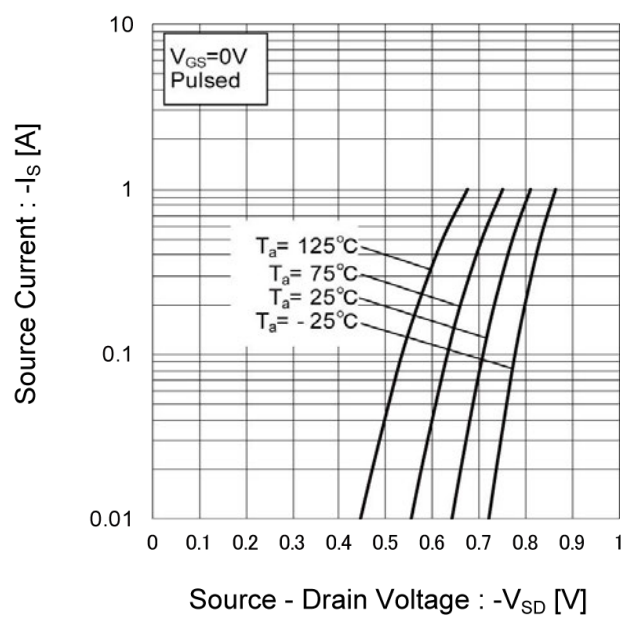


Fig.20 Source Current vs. Source Drain Voltage



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

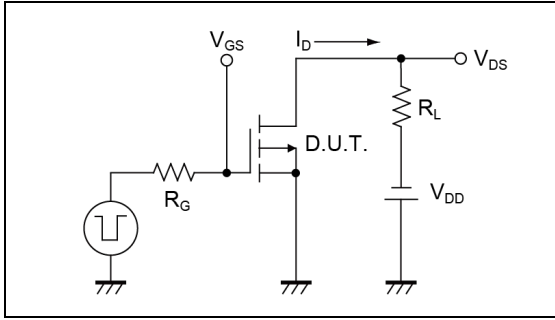


Fig.1-2 Switching Waveforms

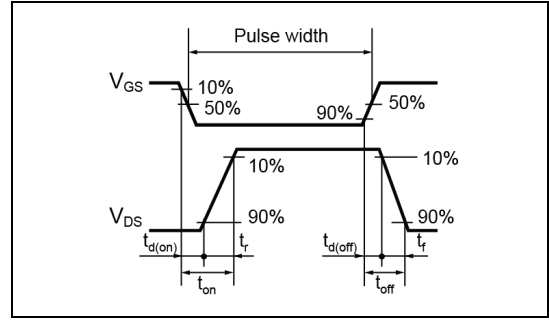


Fig.2-1 Gate Charge Measurement Circuit

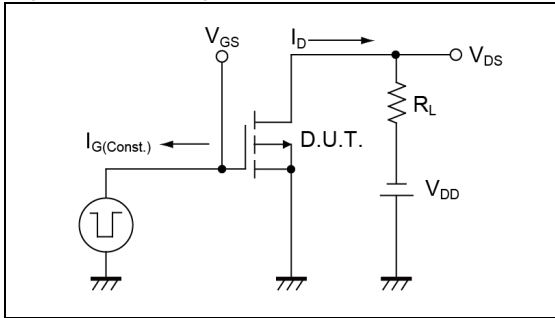


Fig.2-2 Gate Charge Waveform

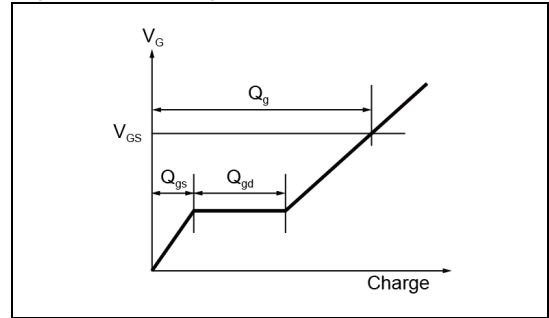


Fig.3-1 Avalanche Measurement Circuit

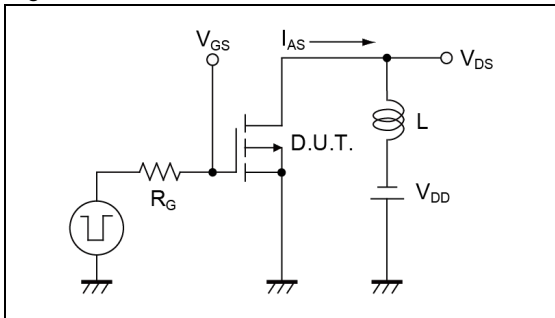
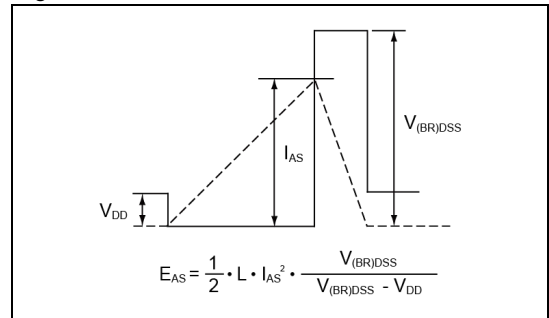
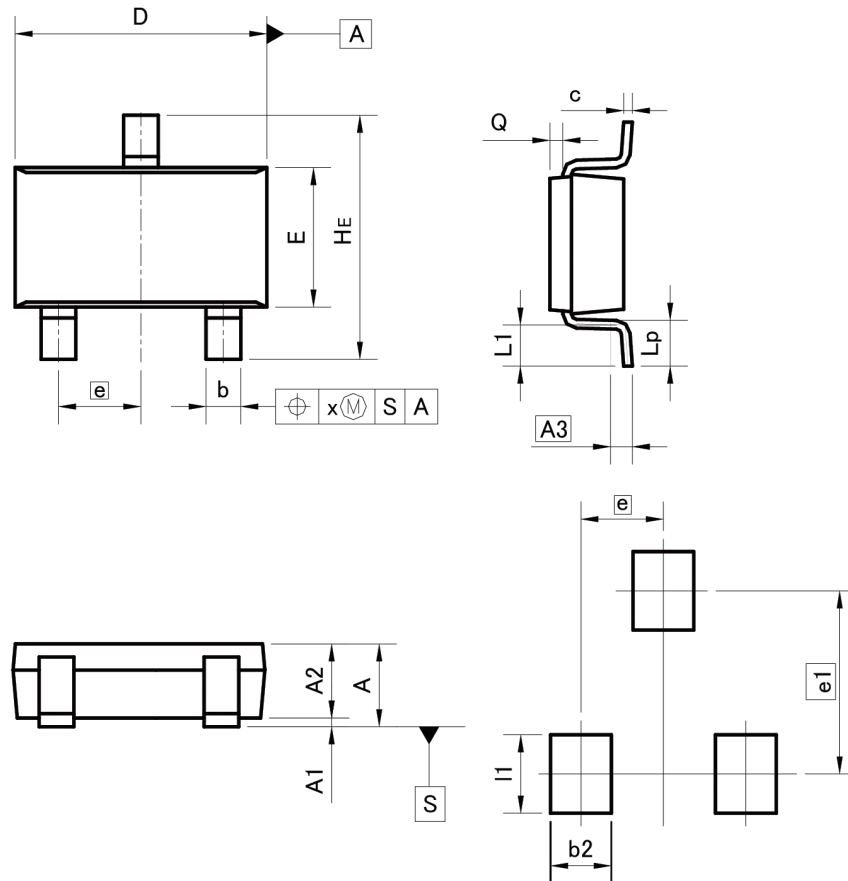


Fig.3-2 Avalanche Waveform



●Dimensions

TSMT3



Pattern of terminal position areas  
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.00	-	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
c	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
x	-	0.20	-	0.008

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.70	-	0.028
e1	2.10		0.083	
l1	-	0.90	-	0.035

Dimension in mm/inches

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